



Product Summary

BV _{DSS}	R _{DS(ON)} Max	Ι _D T _A = +25°C
-12V	$31m\Omega @ V_{GS} = -4.5V$	5.2A
-120	45mΩ @ V _{GS} =-2.5V	4.3A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) while maintaining superior switching performance, which makes the device ideal for high-efficiency powermanagement applications.

Applications

- **DC-DC** Converters
- **Power Management Functions**
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Input Capacitance Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)

P-CHANNEL ENHANCEMENT MODE MOSFET

- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Data Sheet (DMP1045UQ)

Mechanical Data

Case: SOT23

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- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.009 grams (Approximate)

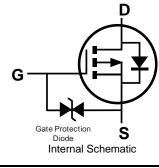




Top View

SOT23





Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1045U-7	SOT23	3,000/Tape & Reel

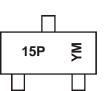
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant. Notes:

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, see http://www.diodes.com/products/packages.html.

Marking Information



15P = Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017)

M = Month (ex: 9 = September)

Date Code Key												
Year	2010	~	20	16	2017	2018	2019	2020) 20)21	2022	2023
Code	Х	~		D	E	F	G	Н			J	K
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	-12	V		
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	Ι _D	4.0 3.1	А
Continuous Drain Current (Note 5) V_{GS} = -2.5V	Steady State	T _A = +25°C T _A = +70°C	ID	3.3 2.6	А
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	ID	5.2 4.2	А
Continuous Drain Current (Note 6) V_{GS} = -2.5V	ID	4.3 3.4	А		
Maximum Continuous Body Diode Forward Current	Is	2	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I _{DM}	40	А		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	168	°C/W
Total Power Dissipation (Note 6)	PD	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	99	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{eJC}	14.8	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-12	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current ($T_J = +25^{\circ}C$)	I _{DSS}	_	—	-1.0	μA	$V_{DS} = -12V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	—	—	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	•			•		÷	
Gate Threshold Voltage	V _{GS(TH)}	-0.3	-0.55	-1.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
			26	31		$V_{GS} = -4.5V, I_D = -4.0A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	31	45	mΩ	$V_{GS} = -2.5V, I_D = -3.5A$	
			45	75		V _{GS} = -1.8V, I _D = -2.7A	
Forward Transfer Admittance	Y _{FS}		12	—	S	$V_{DS} = -5V, I_D = -4A$	
Diode Forward Voltage	V _{SD}	_	-0.6	—	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)			•	•		·	
Input Capacitance	CISS	_	1357	—	pF		
Output Capacitance	C _{OSS}	_	504	_	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C _{RSS}		235	—	pF		
Gate Resistnace	R _G	—	14.1	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS (Note 8)			•	•		·	
Total Gate Charge	Q _G	_	15.8	—	nC		
Gate-Source Charge	Q _{GS}	_	2.0	_	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -4	
Gate-Drain Charge	Q _{GD}	—	3.9	—	nC	7	
Turn-On Delay Time	t _{D(ON)}		15.7	—	ns		
Turn-On Rise Time	t _R	—	23.3	—	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	91.2	—	ns	$R_L = 2.5\Omega, R_G = 3.0\Omega$	
Turn-Off Fall Time	tF	_	106.9	_	ns	1	

Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PCB, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.

Notes:



DMP1045U

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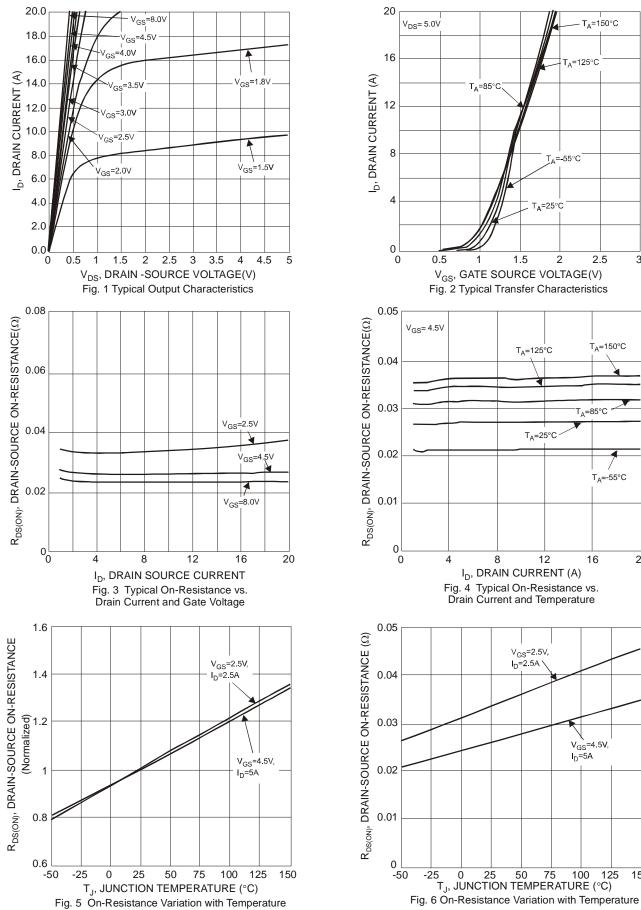
T_A=150°C

T_A=-55°C

20

16

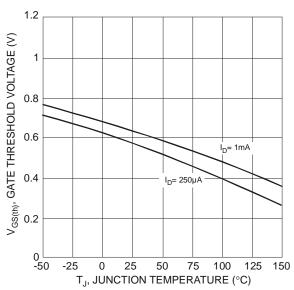
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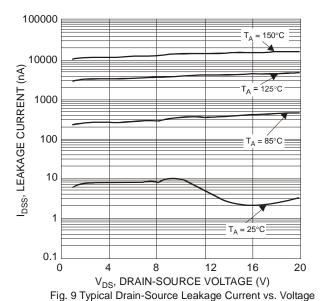
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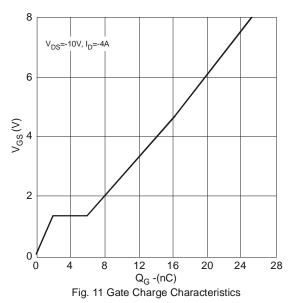
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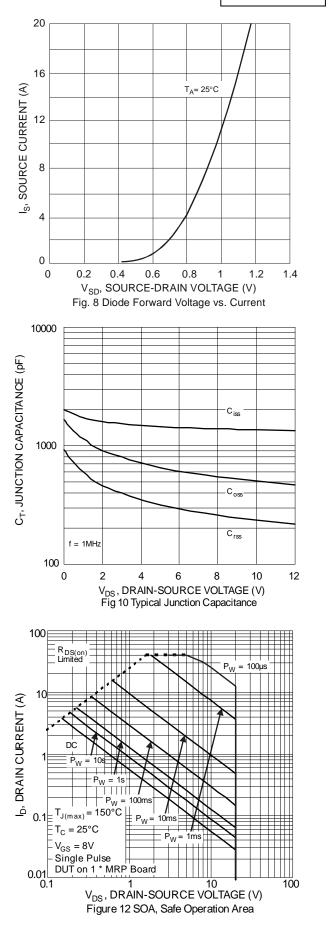




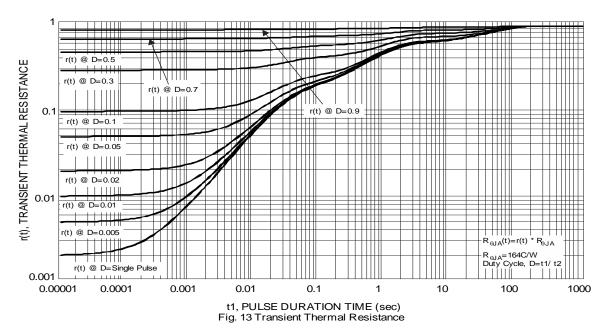








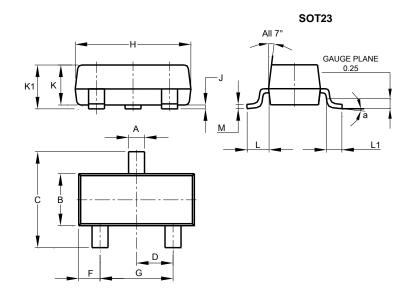






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

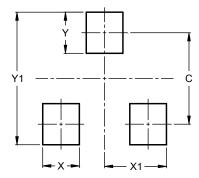


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in		
Dimensions	mm)		
С	2.0		
Х	0.8		
X1	1.35		
Y	0.9		
Y1	2.9		



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